## **Dual P-Channel 30-V (D-S) MOSFET**

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

### **Typical Applications:**

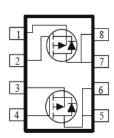
- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
-30	8 @ V <sub>GS</sub> = -10V	-55 <sup>c</sup>	
-30	12 @ $V_{GS} = -4.5V$	-45°	

#### DFN5X6-8L







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			-30	V		
Gate-Source Voltage		$V_{GS}$	±20	V		
	T <sub>A</sub> =25°C	- I <sub>D</sub>	-15 <sup>a</sup>			
Continuous Drain Current	T <sub>A</sub> =70°C		-12 <sup>a</sup>	A		
Continuous Diain Curient	T <sub>C</sub> =25°C		-55 <sup>c</sup>			
	T <sub>C</sub> =70°C		-44 <sup>c</sup>			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	-60				
Continuous Source Current (Diode Conduction) a		Is	-3.3			
	T <sub>A</sub> =25°C		2.5			
Power Dissipation	T <sub>A</sub> =70°C	P <sub>D</sub>	1.6	W		
Power dissipation	T <sub>C</sub> =25°C		36			
	T <sub>C</sub> =70°C		23			
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	D	50	°C/W			
IMAXIIIIUIII JUIICUOII-UO-AITIDIETIU	Steady State	$R_{\theta JA}$	70				
Maximum Junction-to-Case	Steady State	$R_{\theta JC}$	3.5				

1

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board
- b. Pulse width limited by maximum junction temperature
- c. Package limited

#### **Electrical Characteristics**

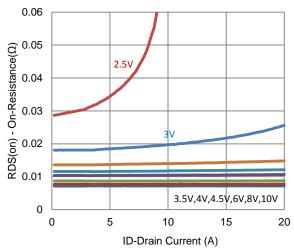
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zoro Coto Voltogo Droin Correct		$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1 uA		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-20			Α	
Dunin Course On Braintain a	r	$V_{GS} = -10 \text{ V}, I_{D} = -9 \text{ A}$			8	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -7.2 \text{ A}$			12	11177	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -9 \text{ A}$		11		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ V}$		-0.76		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$		56		nC	
Gate-Source Charge	$Q_{gs}$	$I_{D} = -9 \text{ A}$		16			
Gate-Drain Charge	$Q_{gd}$	1D = 3 K		20			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -15 \text{ V}, R_{L} = 1.7 \Omega,$		10			
Rise Time	t <sub>r</sub>	$V_{DS} = -13 \text{ V}, \text{ K}_L = 1.7 \Omega,$ $I_D = -9 \text{ A},$		10		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		124		ns	
Fall Time	t <sub>f</sub>	VGEN = 10 V, NGEN = 0 12		41			
Input Capacitance	C <sub>iss</sub>			4450			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$	_	437		рF	
Reverse Transfer Capacitance	C <sub>rss</sub>			331			

#### Notes

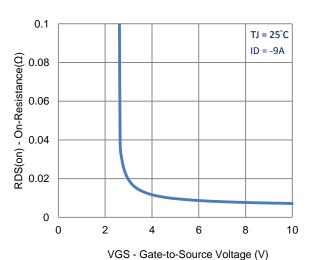
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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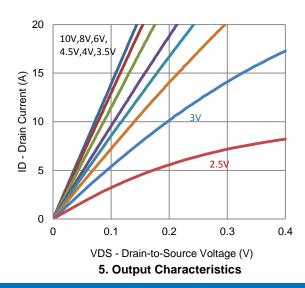
### **Typical Electrical Characteristics**

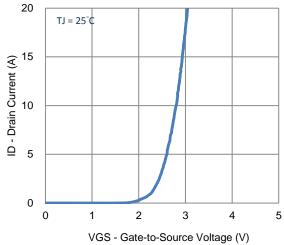


#### 1. On-Resistance vs. Drain Current

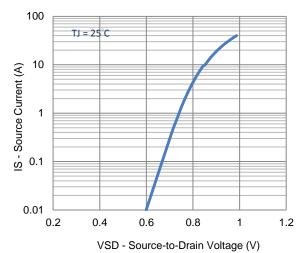


3. On-Resistance vs. Gate-to-Source Voltage

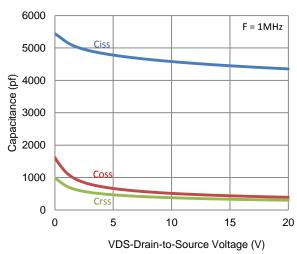




2. Transfer Characteristics

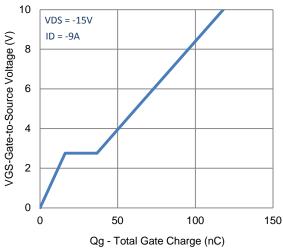


4. Drain-to-Source Forward Voltage

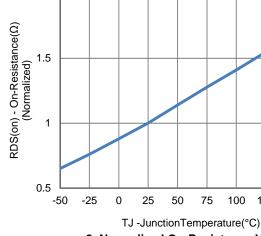


### **Typical Electrical Characteristics**

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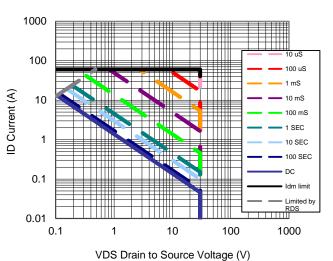
Qg - Total Gate Charge (nC



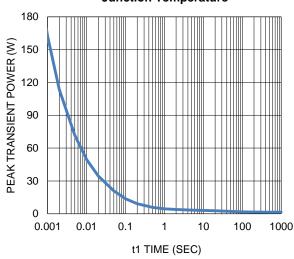
8. Normalized On-Resistance Vs Junction Temperature

125

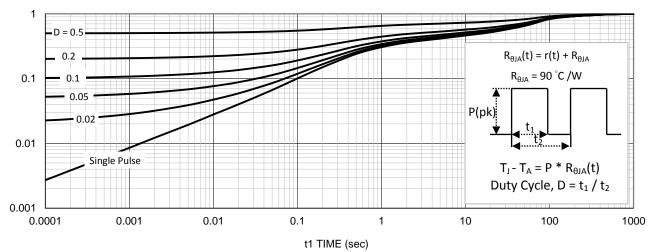
150



9. Safe Operating Area

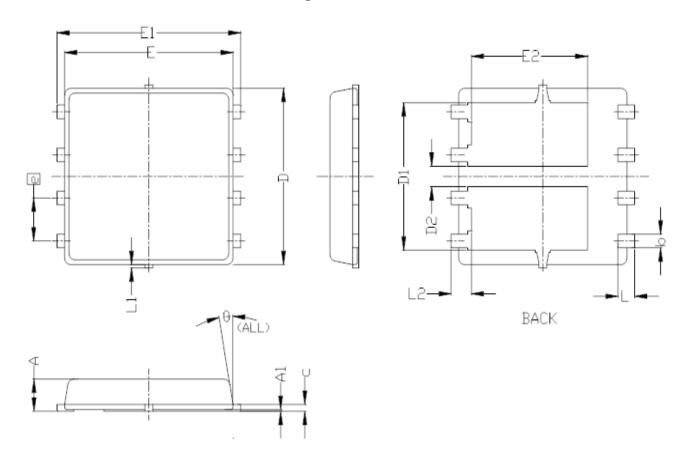


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0. 039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.15	0.20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е	5, 55 BSC			0, 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	